AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Original) A compound semiconductor epitaxial substrate for use in a strain channel high electron mobility field effect transistor, comprising an InGaAs layer as a strain channel layer and an AlGaAs layer containing n-type impurities as an electron supplying layer, wherein said InGaAs layer has an emission peak wavelength at 77 K of 1030 nm or more.

2. (Original) The compound semiconductor epitaxial substrate according to claim 1, wherein GaAs layers are provided as spacer layers in contact with a top surface and a bottom surface of said InGaAs layer, respectively.

3. (Original) The compound semiconductor epitaxial substrate according to claim 2, wherein each of said GaAs layers has a thickness of 4 nm or more.

4. (Original) The compound semiconductor epitaxial substrate according to claim 1, wherein said InGaAs layer has an electron mobility at 300 K of 8300 $cm^2/V \cdot s$ or more.

5. (currently amended) A method for manufacturing ~~the~~ a compound semiconductor epitaxial substrate ~~according to claim 1, 2, 3, or 4~~ that comprises an InGaAs layer as a strain channel layer and an AlGaAs layer containing n-type impurities as an electron supplying layer, wherein said InGaAs layer has an emission peak wavelength at 77 K of 1030 nm or more, said method comprising epitaxially growing each compound semiconductor layer by employing a metalorganic chemical vapor deposition (MOCVD) method.

6. (new) The method according to Claim 5, wherein GaAs layers are provided as spacer layers in contact with a top surface and a bottom surface of said InGaAs layer, respectively.

7. (new) The method according to Claim 6, wherein each of said GaAs layers has a thickness of 4 nm or more

8. (new) The method according to Claim 5, wherein said InGaAs layer has an electron mobility at 300 K of 8300 $cm^2/V \cdot s$ or more.